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| FORM PTS-1449 US Dept. of Commerce<br>Patent and Trademark Office         |  |  | ATTORNEY DOCKET NO.<br>221-Div.                 | SERIAL NO.<br>09/483,859 |
| INFORMATION DISCLOSURE STATEMENT<br><br>(use several sheets if necessary) |  |  | APPLICANT<br>Gautam Bhandari and Thomas H. Baum |                          |
|   |  |  | FILING DATE<br>January 17, 2000                 | GROUP<br>TBA             |

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| INFORMATION DISCLOSURE STATEMENT<br><br>APR 11 2000 (use several sheets if necessary)   |                    |   | APPLICANT                          |       |                 |                               |          |
|   |                    |   | Gautam Bhandari and Thomas H. Baum |       |                 |                               |          |
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|   |                    |   | January 17, 2000                   |       | TBA 1762        |                               |          |
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| <i>R. H. Baetz</i>  |                    |   |                                    |       | <i>3/2/01</i>   |                               |          |
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| EXAMINER<br><i>R. R. Schrock</i>  | PATENT NUMBER<br>CI 3,988,332 | ISSUE DATE<br><i>1972 10 19 76</i>   | NAME<br>R. R. Schrock                           | CLASS<br><i>260</i>              | SUBCLASS<br><i>429R</i>  | FILING DATE IF APPROPRIATE<br><i>IC 1700 APR 18 2000</i> |
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